

SACRIFICIAL INORGANIC POLYMER INTERMETAL DIELECTRIC DAMASCENE WIRE AND VIA LINER

Abstract

The present invention provides a method of forming a rigid interconnect structure, and the device therefrom, including the steps of providing a lower metal wiring layer having first metal lines positioned within a lower low-k dielectric; depositing an upper low-k dielectric atop the lower metal wiring layer; etching at least one portion of the upper low-k dielectric to provide at least one via to the first metal lines; forming rigid dielectric sidewall spacers in at least one via of the upper low-k dielectric; and forming second metal lines in at least one portion of the upper low-k dielectric. The rigid dielectric sidewall spacers may comprise of SiCH, SiC, SiNH, SiN, or SiO₂. Alternatively, the via region of the interconnect structure may be strengthened with a mechanically rigid dielectric comprising SiO₂, SiCOH, or doped silicate glass.